



- VR 100V
- I_{FAV} single diode loaded 215mA
double diode loaded 125mA

Repetitive peak reverse voltage	V _{RRM}	V		100
Reverse voltage	V _R	V	IR=100uA	100
Peak forward surge current	IFSM	A	Non-Repetitive t = 1 μs	4
Average forward current	I _{FAV}	mA	single diode loaded	215
			double diode loaded	125
Power dissipation	P _{tot}	mW		250
Maximum junction temperature	T _j			150
Storage temperature range	T _{stg}			-55 to +150

■ T_a=25 Unless otherwise specified

Breakdown Voltage	V _R	V	IR=100uA	100	
Forward Voltage	V _F	V	IF=1mA		0.9
			IF=10mA		1.0
			IF=50mA		1.1
			IF=150mA		1.25
Reverse Leakage Current	I _R	nA	VR=75V		5
Capacitance	C	pF	VR=0V,f=1MHz		4

Revers

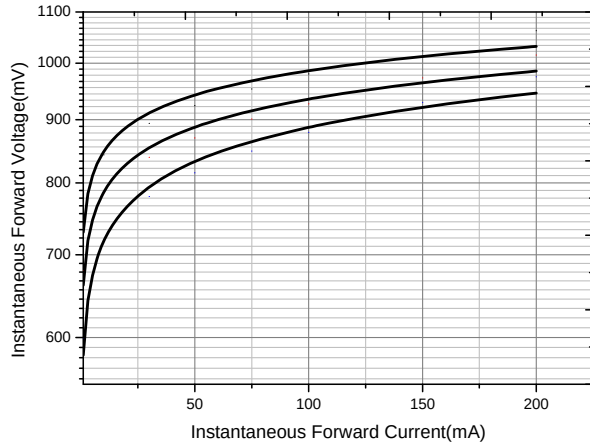


■ (Example)

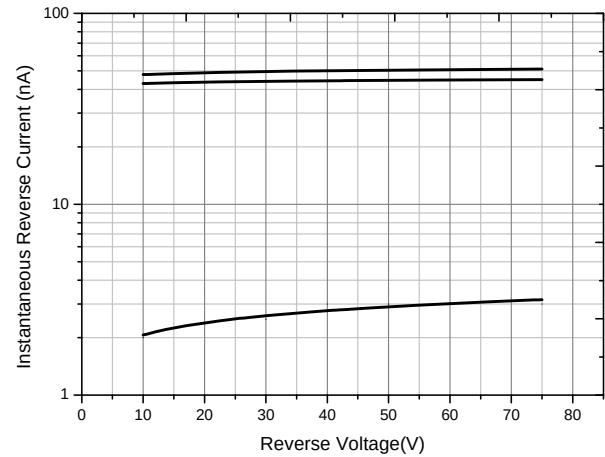
	F2	Approximate 0.008	3000	30000	120000	7" reel

■ (Typical)

Typical Instantaneous Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance

